



PRELIMINARY

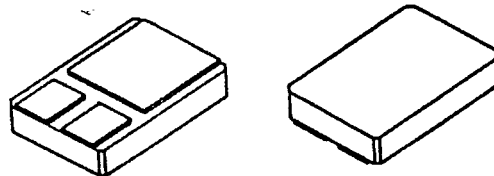
SOLID STATE DEVICES, INC

14849 Firestone Boulevard • La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) • Fax: (714) 522-7424**Designer's Data Sheet****FEATURES:**

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed surface mount power package
- Low inductance leads
- TX, TXV and Space Level screening available
- Replaces: IRF440 Types

SFF440

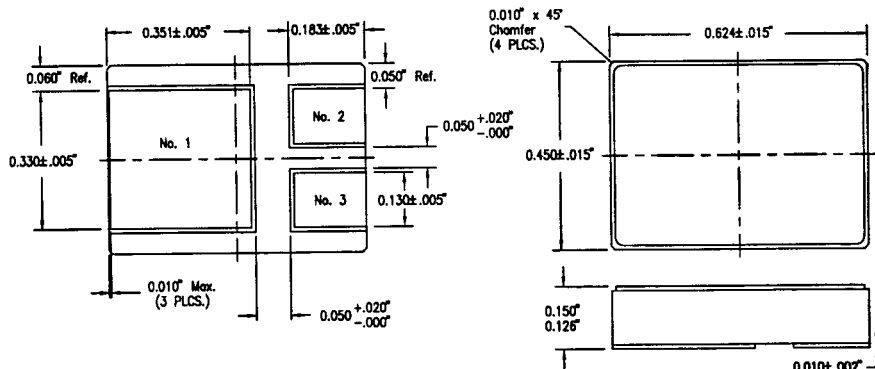
**8 AMP
500 VOLTS
0.85Ω
N-CHANNEL
POWER MOSFET**

MILPACK**MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	500	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current @25°C @100°C	I _D	8 5	Amps
Operating and Storage Temperature	T _{OP} & T _{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	1.7	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P _D	74 55	Watts
Single Pulse Avalanche Energy	E _{AS}	3.6	mJ
Repetitive Avalanche Energy	E _{AR}	---	

PACKAGE OUTLINE: MILPACK**PIN OUT:**

**PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE**



NOTE: All specifications are subject to change without notification. SSDI's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00083 C**MED**

SFF440

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SSDI**SOLID STATE DEVICES, INC**14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**ELECTRICAL CHARACTERISTICS @ T_J=25°C (Unless Otherwise Specified)**

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (V _{GS} =0 V, I _D =250μA)		BV _{DSS}	500	---	---	V
Temperature Coefficient of Breakdown Voltage		$\frac{\Delta BV_{DSS}}{\Delta T_J}$	---	0.78	---	V/°C
Drain to Source on State Resistance @ 5 A (V _{GS} =10 V) @ 8 A		R _{DS(on)}	---	0.70 ---	0.85 0.98	Ω
Gate Threshold Voltage (V _{DS} =V _{GS} , I _D =250μA)		V _{GS(th)}	2.0	---	4.0	V
Forward Transconductance (V _{DS} ≥ 10V, I _{DS} =5 A)		g _{fs}	4.7	7.4	---	S(Ω)
Zero Gate Voltage Drain Current (V _{DS} =80% rated voltage, V _{GS} =0 V) (V _{DS} =80% rated V _{DS} , V _{GS} =0 V, T _A =125°C)		I _{DSS}	---	---	25 250	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated V _{GS}	I _{GSS}	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	V _{GS} =10 Volts 50% rated V _{DS} I _D =8 A	Q _g Q _{gs} Q _{gd}	27.3 2 11	34 6 17	68.5 12.5 42	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	V _{DD} =50% rated V _{DS} I _D = 8 A R _G =9.1Ω	t _{d(on)} t _r t _{d(off)} t _f	---	22 27 42 15	45 49 72 51	nsec
Diode Forward Voltage (I _S =rated I _D , V _{GS} =0 V, T _J =25°C)		V _{SD}	---	---	1.5	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C I _F =rated I _D di/dt=100 A/μsec	t _{rr} Q _{RR}	---	380 3	700 8.9	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{GS} =0 Volts V _{DS} =25 Volts f= 1 MHz	C _{iss} C _{oss} C _{rss}	---	1300 310 120	---	pF

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.